



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

WBFBP-02C Plastic-Encapsulate Diodes

DK400LED02 Schottky barrier Diodes

DESCRIPTION

Silicon epitaxial planar

FEATURES

- Small surface mounting type
- High Speed
- High reliability with high surge current handing capability

APPLICATION

High speed switching For Detection

For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)

MARKING: 7



WBFBP-02C

(1.0×0.6×0.5)

unit: mm



Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25°C

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V _{RM}	90	V
DC reverse voltage	V _R	80	V
Peak forward current	I _{FM}	225	mA
Mean rectifying current	I _O	100	mA
Surge current (1s)	I _{surge}	500	mA
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55~+125	°C

Electrical Ratings @T_A=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _F			1.2	V	I _F =100mA
Reverse current	I _R			0.1	μA	V _R =80V
Capacitance between terminals	C _T			3.0	pF	V _R =0.5V, f=1MHz
Reverse recovery time	t _{rr}			4	ns	V _R =6V, I _F =10mA, R _L =100Ω

Typical Characteristics

●Electrical characteristic curves (Ta = 25°C)

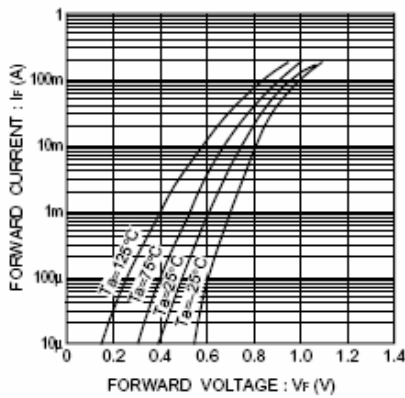


Fig.1 Forward characteristics

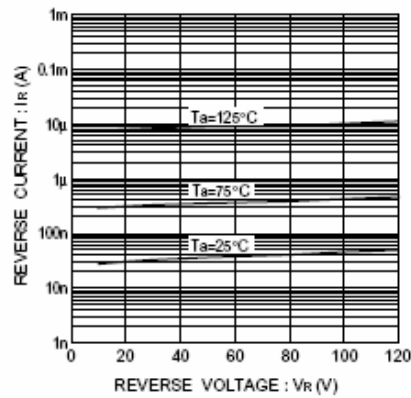


Fig.2 Reverse characteristics

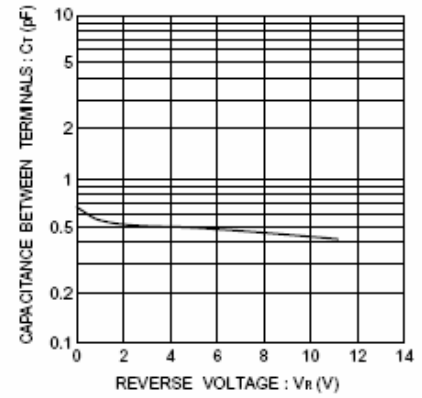


Fig.3 Capacitance between terminals

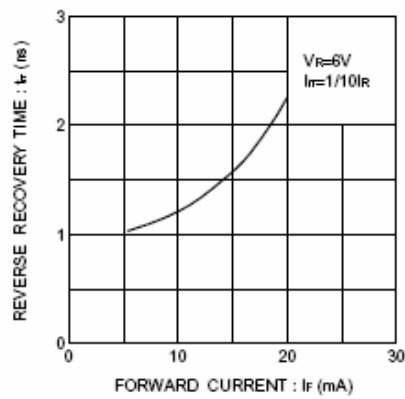


Fig.4 Reverse recovery time characteristics

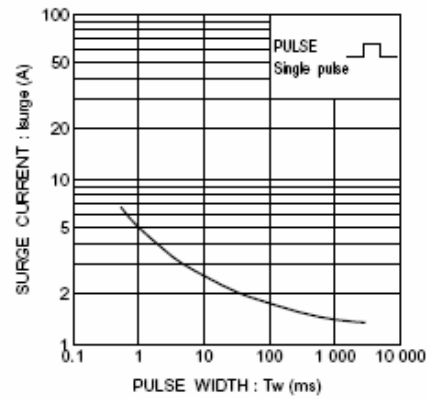


Fig.5 Surge current characteristics

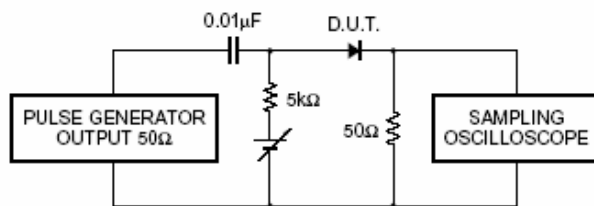


Fig.6 Reverse recovery time (t_r) measurement circuit